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- (71) Applicant (for all designated States except US): KONIN-KLIJKE PHILIPS ELECTRONICS, N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).
- (71) Applicant (for AE only): U.S. PHILIPS CORPORA-TION [US/US]; 1251 Avenue of the Americas, New York, NY 10020 (US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): EUEN, Wolfgang [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL). GROSS, Stephan [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

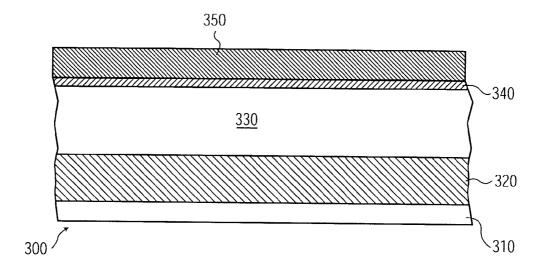
- (74) Common Representative: KONINKLIJKE PHILIPS ELECTRONICS, N.V.; c/o Daniel L. Michalek 1109 McKay Drive, M/S-41SJ, San Jose, CA 95131-1706 (US).
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Declarations under Rule 4.17:

 as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))

[Continued on next page]

(54) Title: REDUCTION OF SHEET RESISTANCE OF PHOSPHORUS IMPLANTED POLY-SILICON



(57) Abstract: There is a process for reducing the sheet resistance of phosphorus-implanted polysilicon. In an example embodiment, there is an MOS transistor structure (300). The structure has a gate region, drain region and a source region. A method (220) for reducing the sheet resistance of the gate region comprises depositing intrinsic amorphous silicon (221) at a predetermined temperature onto the gate region. An amorphizing species is implanted (222) into the intrinsic amorphous silicon. Phosphorus species are then implanted (223) into the gate region of the MOS transistor structure. A feature of this embodiment includes using Ar+ as the amorphizing species.

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INTERNATIONAL SEARCH REPORT

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CLASSIFICATION OF SUBJECT MATTER NV. H01L21/28 H01L2 H01L21/3215 H01L29/49 H01L21/265 According to International Patent Classification (IPC) or to both national classification and IPC **B. FIELDS SEARCHED** Minimum documentation searched (classification system followed by classification symbols) H01L Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Electronic data base consulted during the international search (name of data base and, where practical, search terms used) EPO-Internal C. DOCUMENTS CONSIDERED TO BE RELEVANT Category* Citation of document, with indication, where appropriate, of the relevant passages Relevant to claim No. US 5 959 333 A (GARDNER ET AL) 1 - 10X 28 September 1999 (1999-09-28) column 5, line 4 - line 60; figure 2 column 1, line 43 - column 2, line 38 11 US 5 254 484 A (HEFNER ET AL) Α 19 October 1993 (1993-10-19) column 2, line 32 - line 67 abstract US 4 689 667 A (ARONOWITZ ET AL) 11 Υ 25 August 1987 (1987-08-25) abstract column 3, line 21 - line 30 US 6 720 626 B1 (IGARASHI MOTOSHIGE) 2,6,7 Α 13 April 2004 (2004-04-13) figures 1-8 χ Further documents are listed in the continuation of Box C. See patent family annex. Special categories of cited documents: "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the "A" document defining the general state of the art which is not considered to be of particular relevance invention earlier document but published on or after the international "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such docu-"O" document referring to an oral disclosure, use, exhibition or ments, such combination being obvious to a person skilled document published prior to the international filing date but later than the priority date claimed "&" document member of the same patent family Date of the actual completion of the international search Date of mailing of the international search report 30 June 2006 19/07/2006 Authorized officer Name and mailing address of the ISA/ European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016

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